



**MCQ set#4:Si Microfabrication (Continue)**

**Choose the most proper answer:**

1. .... is considered as the most expensive micromechanical process:  
a) Etching  
b) Lift-off technique  
c) Lithography  
d) Masking
2. Lithography is used for:  
a) Forming resist layers on the substrate  
b) Cutting tool  
c) Forming electric bonds  
d) None of the above
3. Types of lithography:  
a) Photolithography  
b) X-ray lithography  
c) E-beam lithography  
d) All of the above
4. Types of photoresist:  
a) Positive  
b) Negative  
c) a & b  
d) None of the above
5. In X-ray lithography, the X-ray absorber is usually:  
a) Silver  
b) Gold  
c) Aluminum  
d) None of the above
6. .... is projecting electron beam directing on photoresist of the wafer :  
a) E-beam lithography  
b) Light emitting  
c) Electron beam gun  
d) Radar beam
7. The electron gun is used in lithography because it is..... :  
a) Inexpensive  
b) Accurate  
c) Doesn't require high voltage  
d) Not e of the above
- 8.....Used for removing desired areas of the photo resist from the substrate:  
a) LIGA  
b) Lithography  
c) Etching  
d) Not e of the above
9. Types of etching are.....:  
a) Wet isotropic  
b) Wet anisotropic  
c) Dry  
d) All of the above
10. The most widely used anisotropic etchant is/are.....:  
a) KOH  
b) KCl  
c) NaOH  
d) a&c
11. Etching is always anisotropic if the material is.....:  
a) Crystalline  
b) Polycrystalline  
c) Amorphous  
d) None of the above
12. ....is an Etch stop technique.  
a) Wet isotropic etching.  
b) Wet anisotropic etching.  
c) Electrochemical etching.  
d) Physical sputter etching.
- 13.....is the etching through chemical or physical interaction between ions:  
a) Wet isotropic etching  
b) Wet anisotropic etching  
c) Dry etching <  
d) None of the above
14. Methods of dry etching are:  
a) Physical sputter etching  
b) Chemical plasma etching  
c) Combined chemical/physical etching  
d) All of the above
15. .... is used for metals that are hard to etch:  
a) Lift-off technique  
b) Combined physical/chemical etching  
c) Physical sputter etching  
d) Chemical plasma etching